## 1. General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Very fast switching
- Low threshold voltage
- · Trench MOSFET technology
- · ESD protection up to 2 kV

## 3. Applications

- Relay driver
- · High-speed line driver
- High-side loadswitch
- · Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	er transistor							
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-30	V	
$V_{GS}$	gate-source voltage			-8	-	8	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-220	mA	
Static characte	Static characteristics (per transistor)							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -200 \text{ mA}; T_j = 25 \text{ °C}$		-	2.8	4.1	Ω	

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	0 5 4	D1 D2
2	G1	gate TR1	6 5 4	
3	D2	drain TR2		$G_1$ $\downarrow$
4	S2	source TR2		\ \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
5	G2	gate TR2	1 2 3	
6	D1	drain TR1	SOT666	S1 S2 017aaa260

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
NX3008PBKV	SOT666	plastic, surface-mounted package; 6 leads; 0.5 mm pitch; 1.6 mm x 1.2 mm x 0.55 mm body	SOT666			

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
NX3008PBKV	AB

### 30 V, 220 mA dual P-channel Trench MOSFET

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	tor					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-30	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-220	mA
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-140	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-0.9	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	330	mW
			[1]	-	390	mW
		T <sub>sp</sub> = 25 °C		-	1090	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	500	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-220	mA
ESD maxim	num rating			'	'	'
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

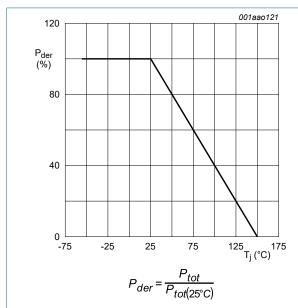


Fig. 1. Normalized total power dissipation as a function of junction temperature

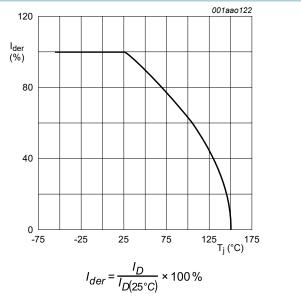
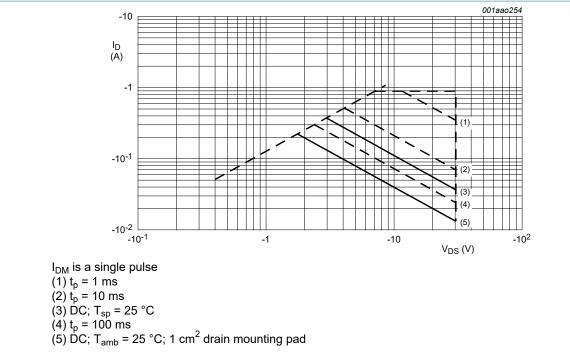


Fig. 2. Normalized continuous drain current as a function of junction temperature

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Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-Fig. 3. source voltage

#### 30 V, 220 mA dual P-channel Trench MOSFET

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

		<b>a</b> 1141			-	2.5	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transiste	or		·	·	·	·	
R <sub>th(j-a)</sub> thermal resistance fr junction to ambient	thermal resistance from	in free air	[1]	-	330	380	K/W
	junction to ambient		[2]	-	280	320	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	115	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

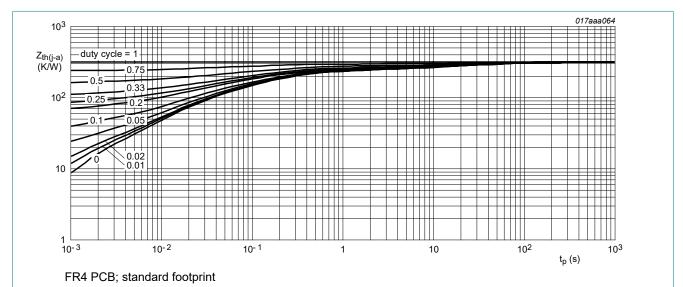


Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

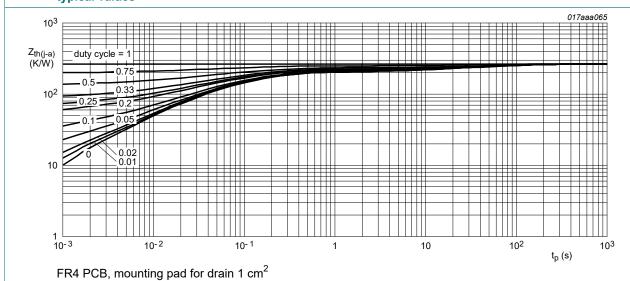


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 30 V, 220 mA dual P-channel Trench MOSFET

## 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.6	-0.9	-1.1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
		V <sub>DS</sub> = -30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	-10	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-0.2	-1	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-0.2	-1	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-10	-	nA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-10	-	nA
		V <sub>GS</sub> = 2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-1	-	nA
		V <sub>GS</sub> = -2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-1	-	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -200 mA; $T_j$ = 25 °C	-	2.8	4.1	Ω
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -200 mA; T <sub>j</sub> = 150 °C	-	5.3	7.8	Ω
		$V_{GS} = -2.5 \text{ V}; I_D = -10 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	5.3	6.5	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -200 \text{ mA}; T_j = 25 \text{ °C}$	-	160	-	mS
Dynamic ch	naracteristics (per transist	or)			'	
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = -15 V; I <sub>D</sub> = -200 mA;	-	0.55	0.72	nC
Q <sub>GS</sub>	gate-source charge	V <sub>GS</sub> = -4.5 V; T <sub>j</sub> = 25 °C	-	0.23	-	nC
$Q_{GD}$	gate-drain charge	1	-	0.09	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	31	46	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	6.5	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	2.3	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -20 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = -4.5 V;	-	19	38	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	30	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	65	130	ns
t <sub>f</sub>	fall time	1	-	38	-	ns
Source-dra	in diode (per transistor)		l	1	1	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = -200 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-0.47	-0.88	-1.2	V

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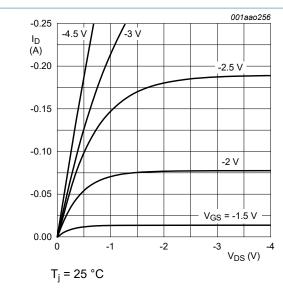
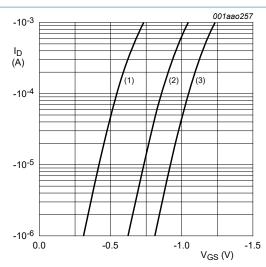


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



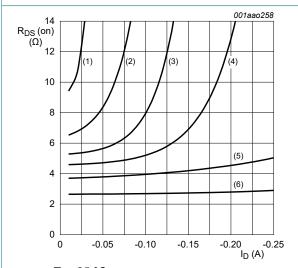
 $T_j = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$ 

(1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25 \, ^{\circ}C$ 

 $(1) V_{GS} = -1.75 V$ 

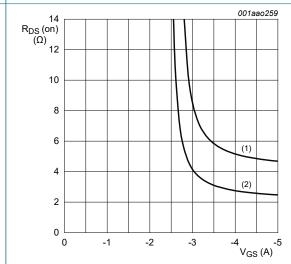
 $(2) V_{GS} = -2.0 V$ 

 $(3) V_{GS} = -2.25 V$ 

 $(4) V_{GS} = -2.5 V$ 

(5)  $V_{GS} = -3.0 \text{ V}$ (6)  $V_{GS} = -4.5 \text{ V}$ 

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = -200 \text{ mA}$ 

(1)  $T_i = 150 \,^{\circ}C$ 

(2)  $T_j = 25$  °C

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 30 V, 220 mA dual P-channel Trench MOSFET

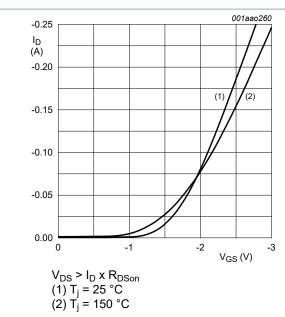


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

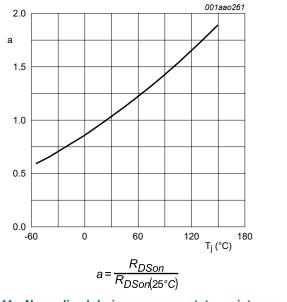
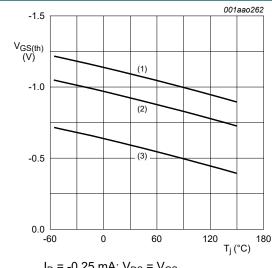


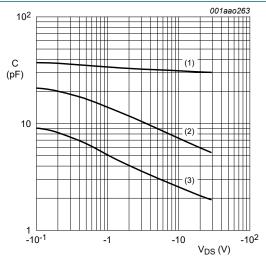
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) Coss
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 30 V, 220 mA dual P-channel Trench MOSFET

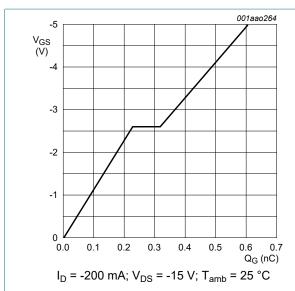


Fig. 14. Gate-source voltage as a function of gate charge; typical values

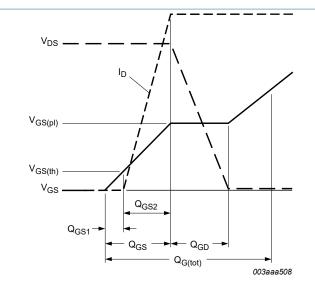
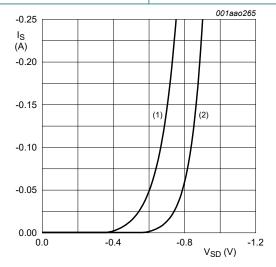


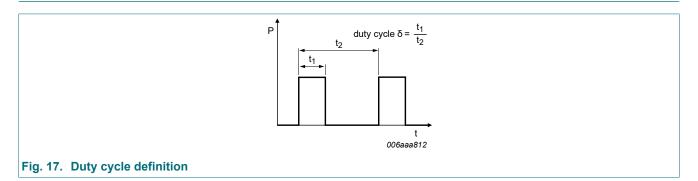
Fig. 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ (2)  $T_j = 25 \,^{\circ}C$ 

Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information



### 30 V, 220 mA dual P-channel Trench MOSFET

# 12. Package outline

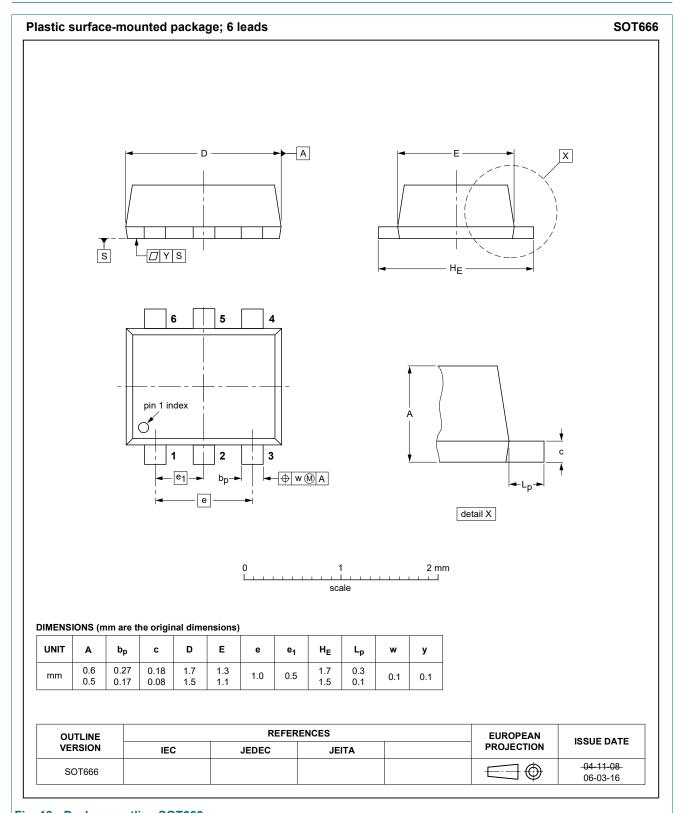
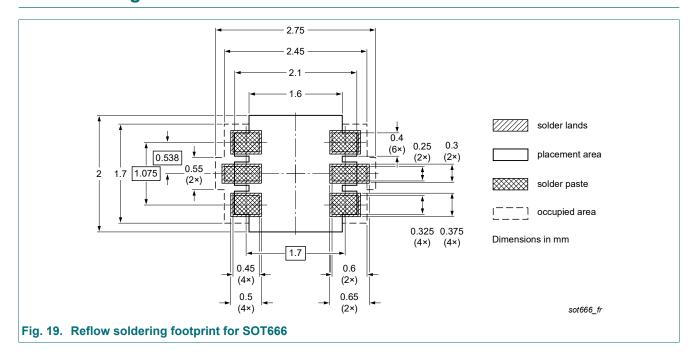


Fig. 18. Package outline SOT666

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# 13. Soldering



## 30 V, 220 mA dual P-channel Trench MOSFET

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
NX3008PBKV v.2	20221228	Product data sheet	-	NX3008PBKV v.1			
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia</li> <li>Legal texts have been adapted to the new company name where appropriate</li> <li>Product changed to non-automotive qualification</li> </ul>						
NX3008PBKV v.1	20110729	Product data sheet	-	-			

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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	Features and benefits

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